



Supplementary Materials

Tungsten-Modulated Molybdenum Selenide/Graphene Heterostructure as an Advanced Electrode for All-Solid-State Supercapacitors

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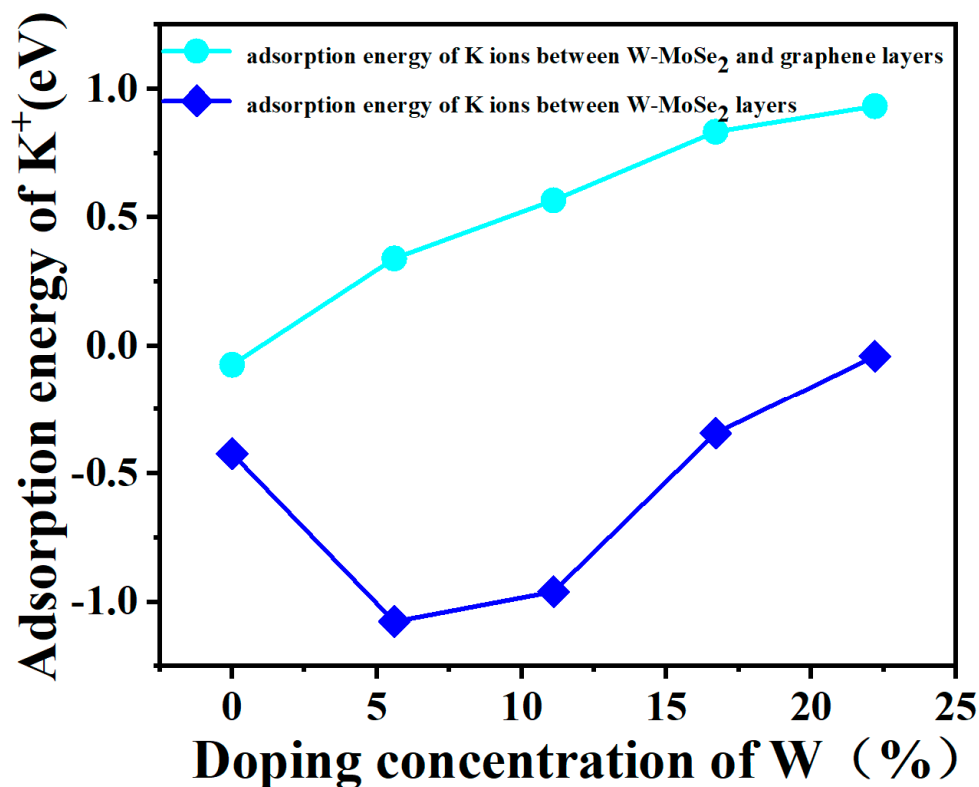


Figure S1. Adsorption energy of K ions under different doping concentrations.

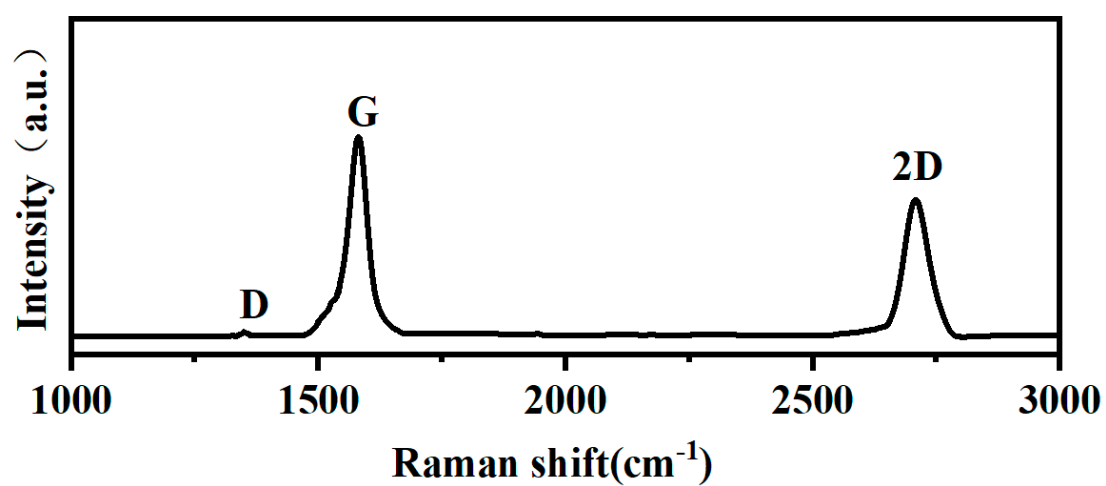


Figure S2. Raman spectra of graphene.

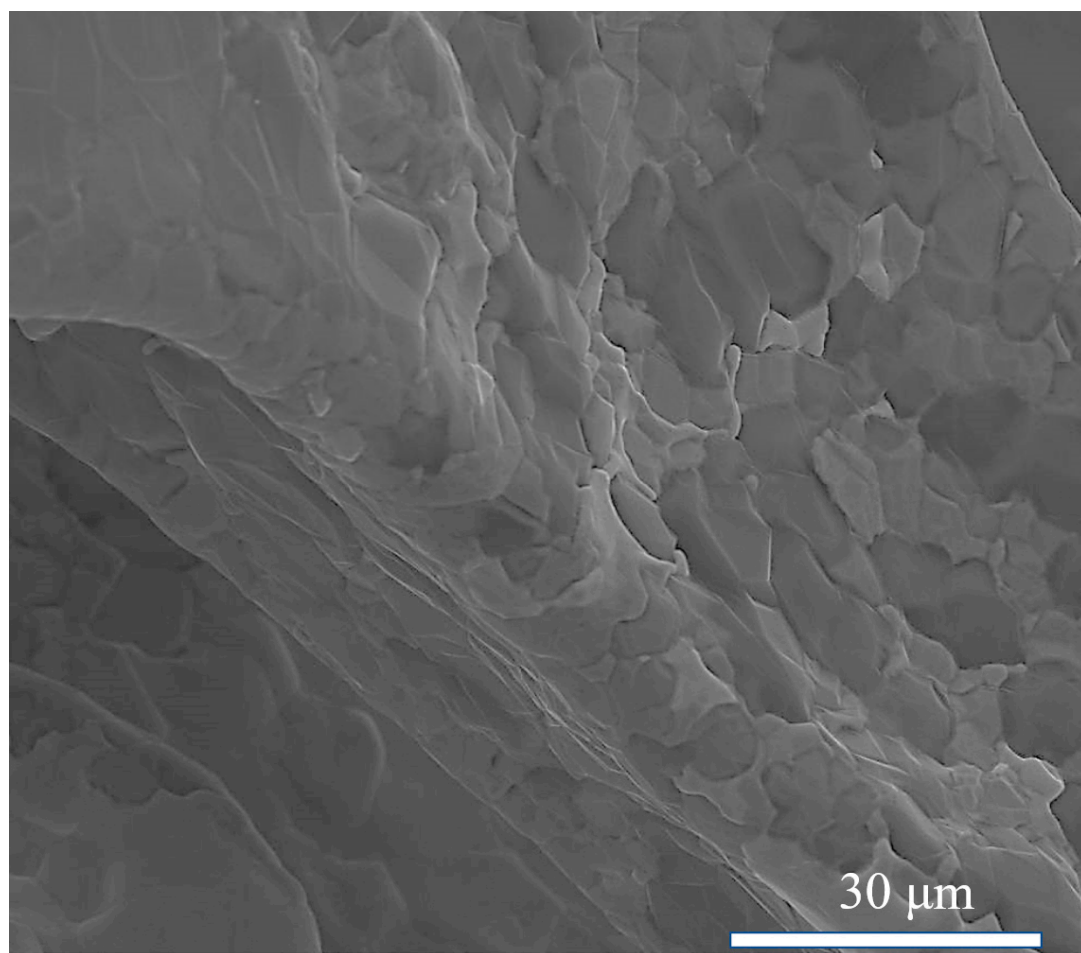


Figure S3. SEM image of graphene.

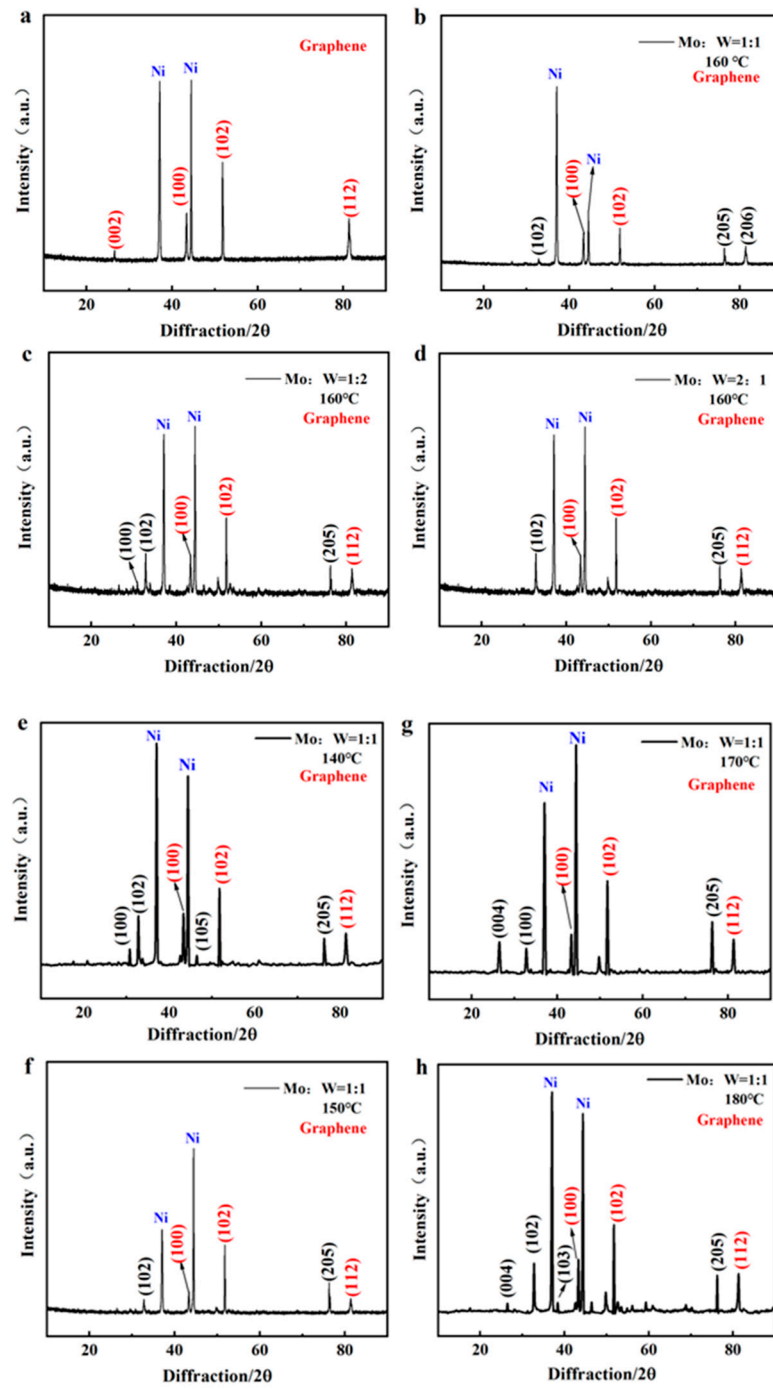


Figure S4. (a) XRD spectrum of Graphene/Ni foam, (b) XRD spectrum of Mo:W = 1:1, (c) XRD spectrum of Mo:W = 1:2, (d) XRD spectrum of Mo:W = 2:1, (e) XRD spectrum of sample grown at 140 °C, (f) XRD spectrum of sample grown at 150 °C, (g) XRD spectrum of sample grown at 170 °C, (h) XRD spectrum of sample grown at 180 °C.

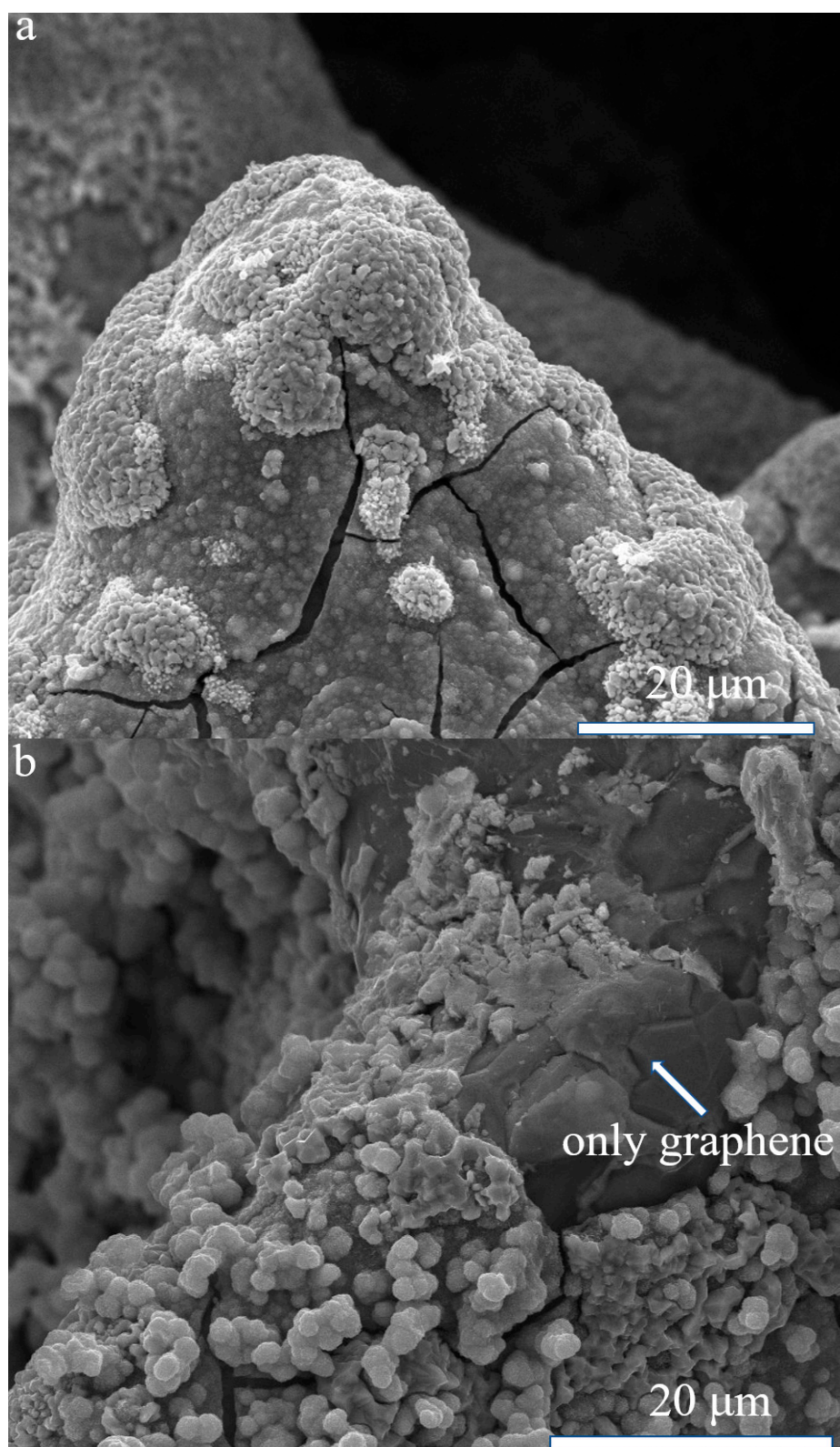


Figure S5. (a) SEM image of device after 5000 cycles, (b) The active material falls off and part of the graphene area is exposed after 5000 cycles.